

| V <sub>RSM</sub> | V <sub>RRM</sub> | V <sub>DRM</sub> | (dv/dt) <sub>cr</sub> | I <sub>TRMS</sub> (maximum values for continuous operation) |               |               |               |
|------------------|------------------|------------------|-----------------------|---|---------------|---------------|---------------|
|                  |                  |                  |                       | 350 A   | 420 A         | 350 A         | 420 A         |
| V                | V                | V/μs             |                       | I <sub>TAV</sub> (sin. 180; T <sub>case</sub> = ...)        |               |               |               |
|                  |                  |                  |                       | 220 A (88 °C)   | 260 A (82 °C) | 220 A (88 °C) | 260 A (82 °C) |
| 900              | 800              | 500              | SKKT                  | SKKT  | SKKH          | SKKH          |               |
| 210/08 D         | 250/08 D         |                  |                       |   | —             | —             |               |
| 1300             | 1200             | 1000             | 210/12 E              | 250/12 E  | 210/12 E      | 250/12 E      |               |
| 1500             | 1400             | 1000             | 210/14 E              | 250/14 E  | 210/14 E      | 250/14 E      |               |
| 1700             | 1600             | 1000             | 210/16 E              | 250/16 E  | 210/16 E      | 250/16 E      |               |
| 1900             | 1800             | 1000             | 210/18 E              | 250/18 E  | 210/18 E      | 250/18 E      |               |
| 2100             | 2000             | 1000             | 210/20 E              | —   | 210/20 E      | —             |               |
| 2300             | 2200             | 1000             | 210/22 E              | —   | 210/22 E      | —             |               |

## SEMIPACK® 3 Thyristor / Diode Modules

SKKT 210      SKKH 210  
 SKKT 250      SKKH 250  
 SKMT 250<sup>1)</sup>



| Symbol                             | Conditions   | SKKT 210<br>SKKH 210                   | SKKT 250<br>SKKH 250 | Units            |
|------------------------------------|--|--|----------------------|------------------|
| I <sub>TAV</sub>                   | sin. 180; (T <sub>case</sub> = ...)  | 210 (90°C)                             | 250 (85°C)           | A                |
| I <sub>D</sub>                     | B2/B6   T <sub>amb</sub> = 35 °C; P 16/170 F   | 420/550                                | 450/585              | A                |
| I <sub>RMS</sub>                   | W1/W3   T <sub>amb</sub> = 35 °C; P 16/170 F   | 526/3 x 440                            | 566/3 x 471          | A                |
| I <sub>TSM</sub>                   | T <sub>vj</sub> = 25 °C; 10 ms   | 8 500                                  | 9 000                | A                |
| i <sup>2</sup> t                   | T <sub>vj</sub> = 130 °C; 10 ms  | 7 500                                  | 8 000                | A                |
|                                    | T <sub>vj</sub> = 25 °C; 8,3 ... 10 ms   | 361 000                                | 405 000              | A <sup>2</sup> s |
|                                    | T <sub>vj</sub> = 130 °C; 8,3 ... 10 ms  | 281 000                                | 320 000              | A <sup>2</sup> s |
| t <sub>gd</sub>                    | T <sub>vj</sub> = 25 °C; I <sub>G</sub> = 1 A<br>dI <sub>G</sub> /dt = 1 A/μs                      | 1                                      |                      | μs               |
| t <sub>gr</sub>                    | V <sub>D</sub> = 0,67 · V <sub>DRM</sub>   | 2                                      |                      | μs               |
| (di/dt) <sub>cr</sub>              | T <sub>vj</sub> = 130 °C   | 250                                    |                      | A/μs             |
| t <sub>q</sub>                     | T <sub>vj</sub> = 130 °C   | typ. 50 ... 150                        |                      | μs               |
| I <sub>H</sub>                     | T <sub>vj</sub> = 25 °C; typ. / max.   | 150 / 500                              |                      | mA               |
| I <sub>L</sub>                     | T <sub>vj</sub> = 25 °C; R <sub>G</sub> = 33 Ω; typ. / max.  | 0,3 / 2                                |                      | A                |
| V <sub>T</sub>                     | T <sub>vj</sub> = 25 °C; I <sub>T</sub> = 750 A  | max. 1,5                               | max. 1,4             | V                |
| V <sub>T(TO)</sub>                 | T <sub>vj</sub> = 130 °C   | 0,95                                   | 0,925                | V                |
| r <sub>T</sub>                     | T <sub>vj</sub> = 130 °C   | 0,6                                    | 0,45                 | mΩ               |
| I <sub>DD</sub> ; I <sub>RD</sub>  | T <sub>vj</sub> = 130 °C; V <sub>RD</sub> = V <sub>RRM</sub><br>V <sub>DD</sub> = V <sub>DRM</sub> | 50                                     | 50                   | mA               |
| V <sub>GT</sub>                    | T <sub>vj</sub> = 25 °C; d.c.  | 3                                      |                      | V                |
| I <sub>GT</sub>                    | T <sub>vj</sub> = 25 °C; d.c.  | 200                                    |                      | mA               |
| V <sub>GD</sub>                    | T <sub>vj</sub> = 130 °C; d.c.   | 0,25                                   |                      | V                |
| I <sub>GD</sub>                    | T <sub>vj</sub> = 130 °C; d.c.   | 10                                     |                      | mA               |
| R <sub>thjc</sub>                  | cont.  | 0,14 / 0,07                            |                      | °C/W             |
|                                    | sin. 180   | 0,15 / 0,075                           |                      | °C/W             |
| R <sub>thch</sub>                  | per thyristor /  | 0,165 / 0,083                          |                      | °C/W             |
| T <sub>vj</sub> , T <sub>stg</sub> | rec. 120   | 0,04 / 0,02                            |                      | °C/W             |
|                                    |  | – 40 ... + 130                         |                      | °C               |
| V <sub>isol</sub>                  | a. c. 50 Hz; r.m.s.; 1 s/1 min   | 3600 / 3000                            |                      | V~               |
| M <sub>1</sub>                     | to heatsink  | 5 (44 lb. in.) ± 15 % <sup>2)</sup>    |                      | Nm               |
| M <sub>2</sub>                     | to terminals   | 9 (80 lb. in.) ± 15 % <sup>3)</sup>    |                      | Nm               |
| a                                  |  | 5 · 9,81                               |                      | m/s <sup>2</sup> |
| w                                  | approx.  | 940                                    |                      | g                |
| Case                               | → page B 1 – 80  | SKKT: A 25<br>SKKH: A 26<br>SKMT: A 64 |                      |                  |

### Features

- Heat transfer through aluminium nitride ceramic isolated metal baseplate
- Precious metal pressure contacts for high reliability
- Thyristor with amplifying gate
- UL recognized, file no. E 63 532

### Typical Applications

- DC motor control (e.g. for machine tools)
- Temperature control (e.g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

<sup>1)</sup> SKMT 250 available on request

<sup>2)</sup> See the assembly instructions

<sup>3)</sup> The screws must be lubricated

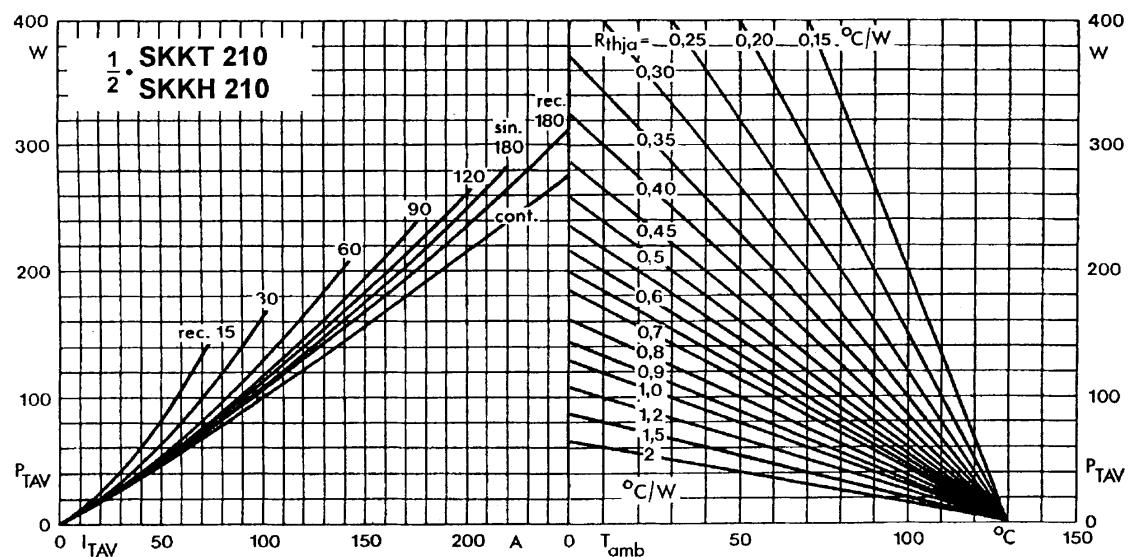


Fig. 1 a Power dissipation per thyristor vs. on-state current and ambient temperature

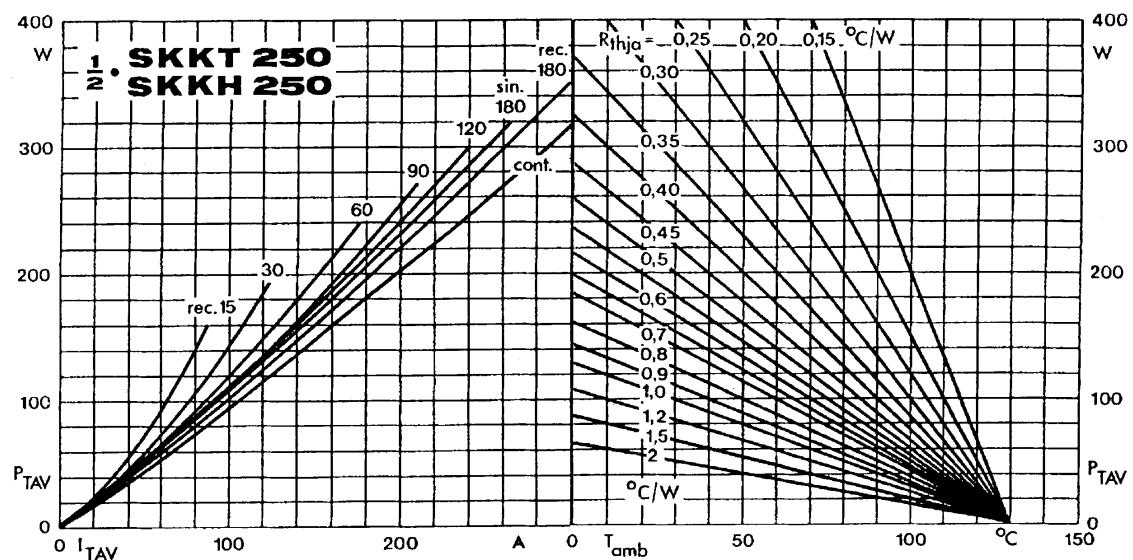


Fig. 1 b Power dissipation per thyristor vs. on-state current and ambient temperature

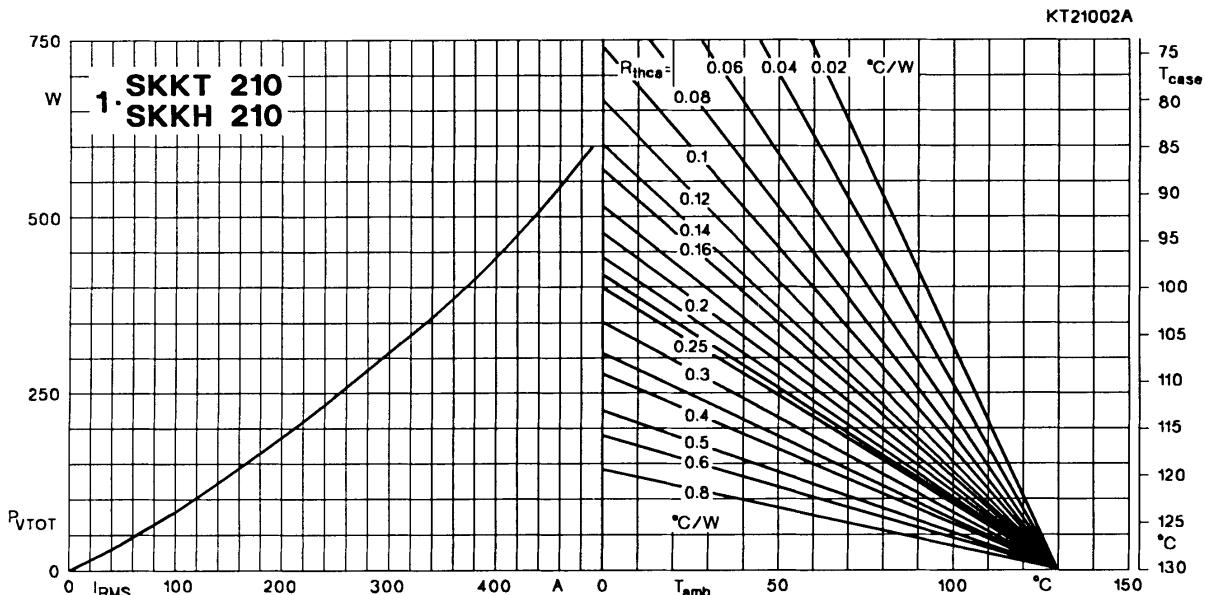


Fig. 2 a Power dissipation per module vs. rms current and case temperature

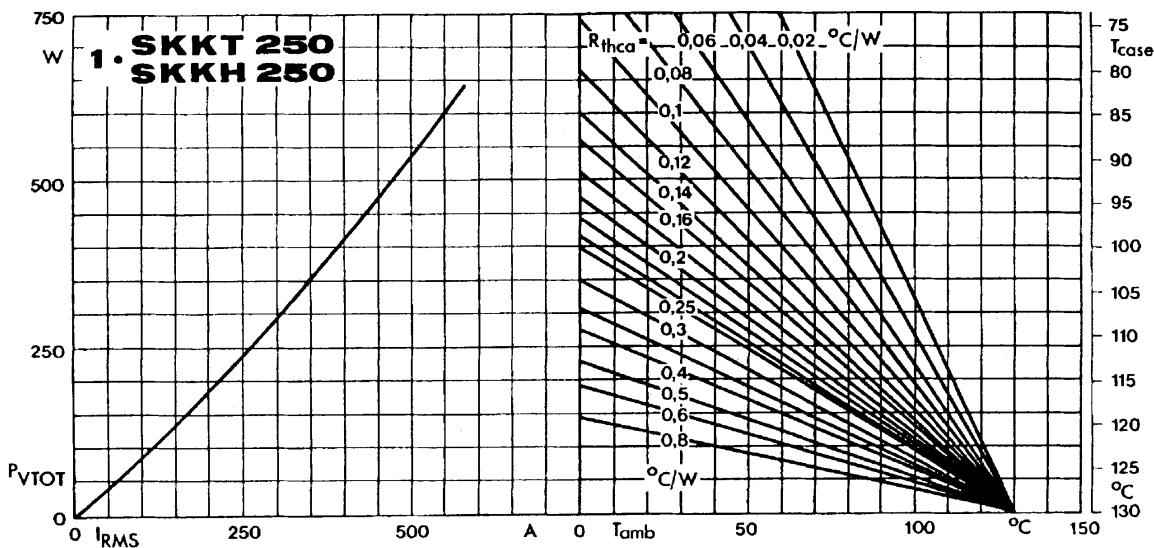


Fig. 2 b Power dissipation per module vs. rms current and case temperature

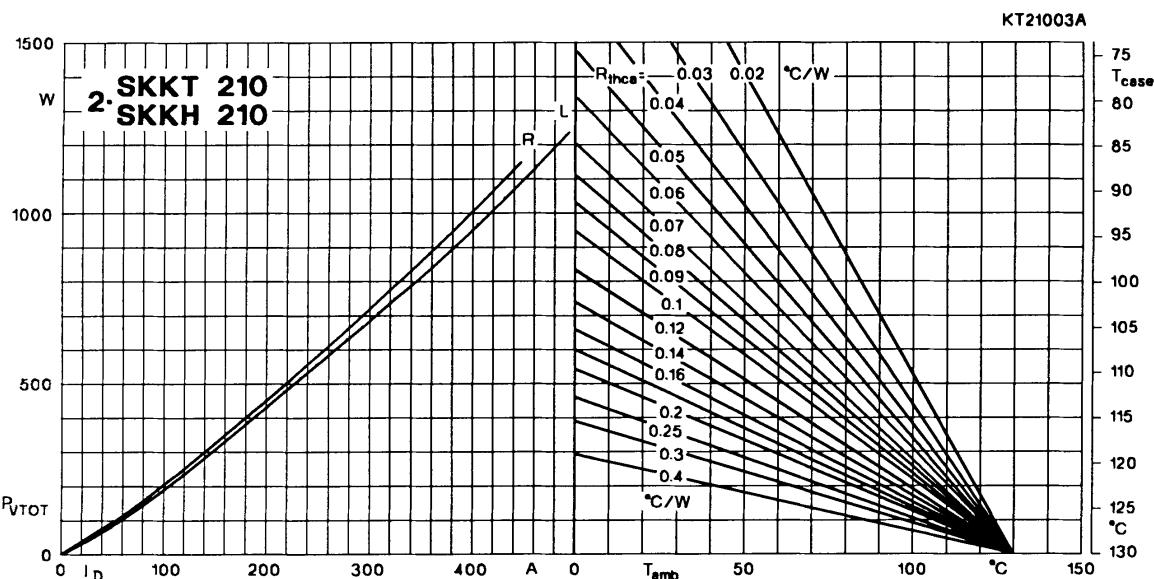


Fig. 3 a Power dissipation of two modules vs. direct current and case temperature

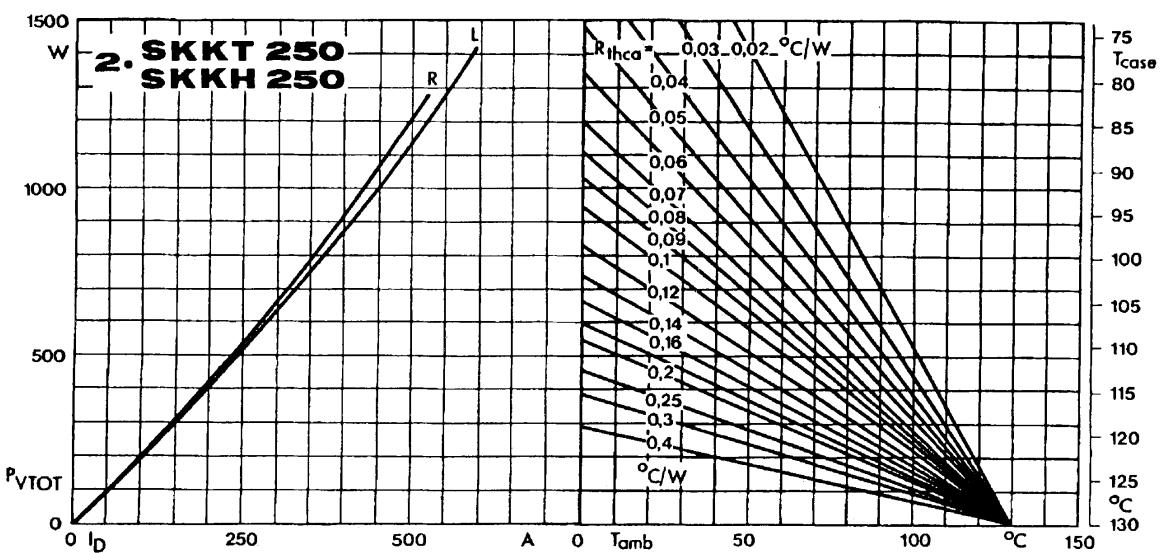


Fig. 3 b Power dissipation of two modules vs. direct current and case temperature

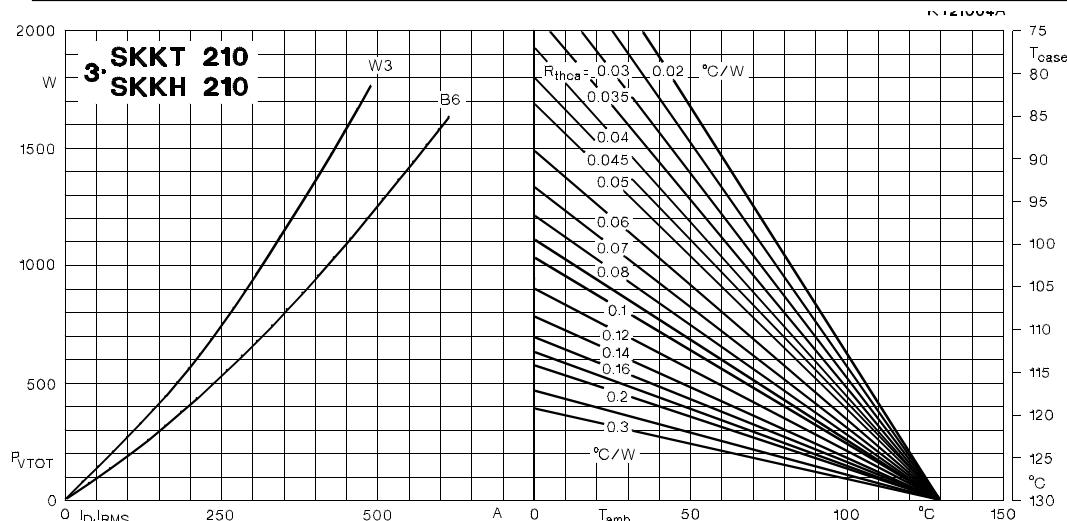


Fig. 4 a Power dissipation of three modules vs. direct and rms current and case temperature

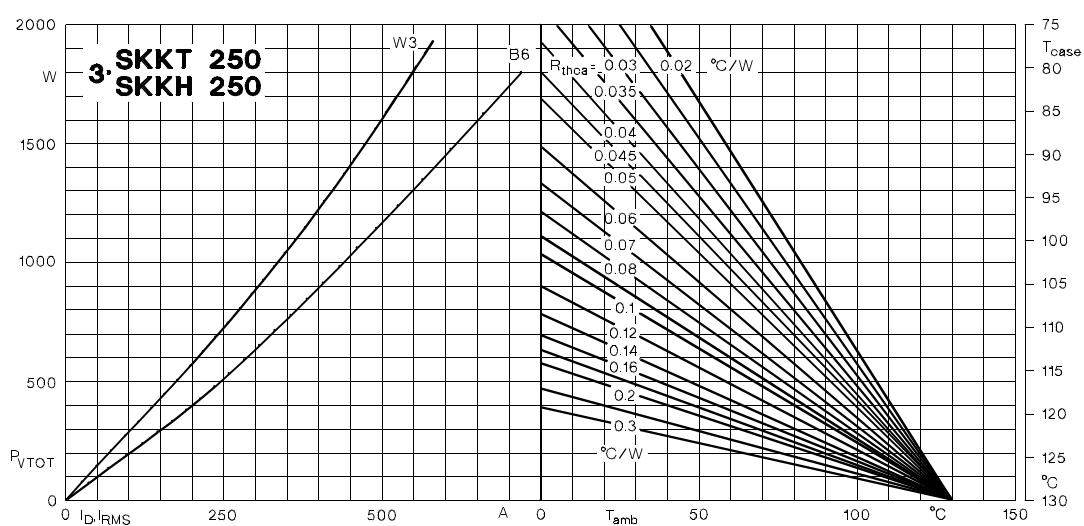


Fig. 4 b Power dissipation of three modules vs. direct and rms current and case temperature

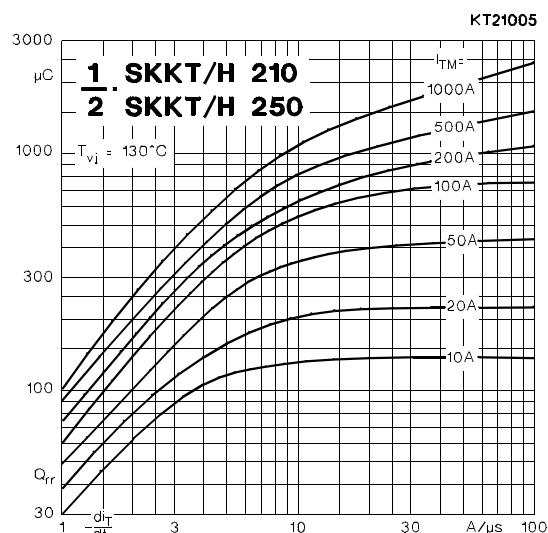


Fig. 5 Recovered charge vs. current decrease

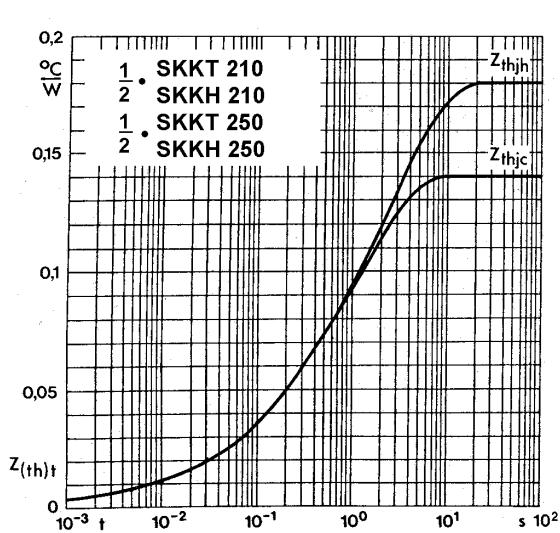
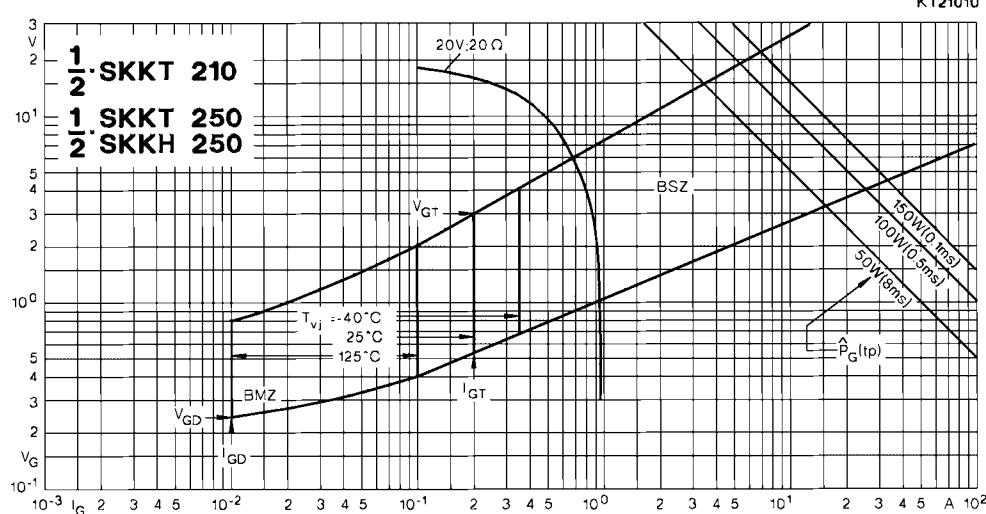
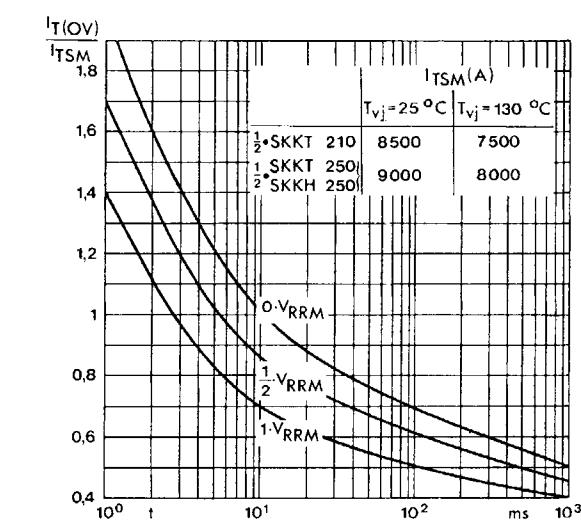
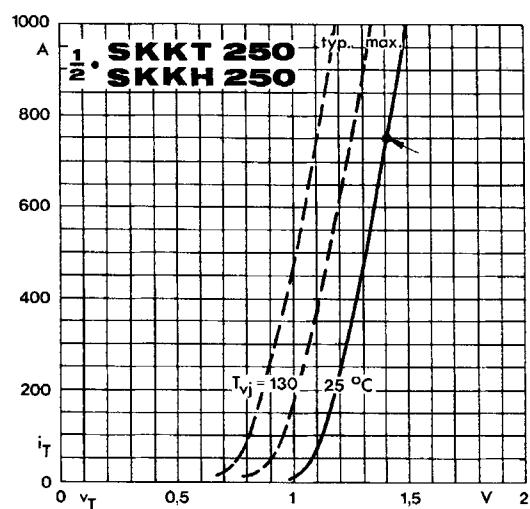
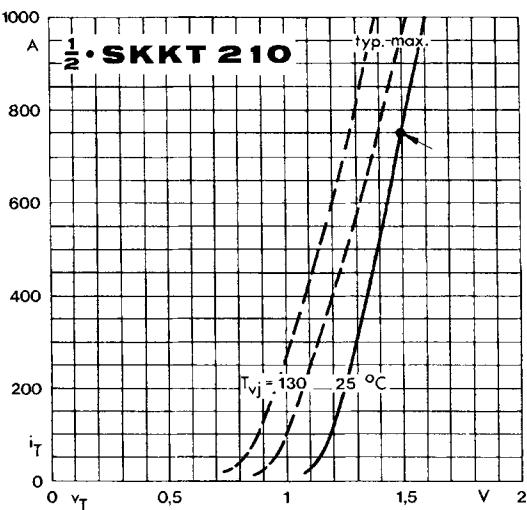
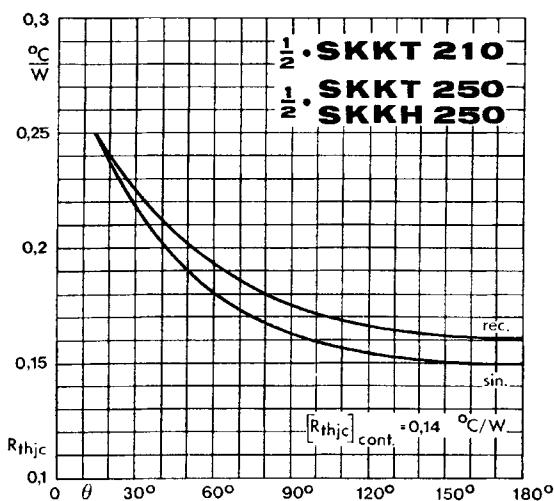


Fig. 6 Transient thermal impedance vs. time

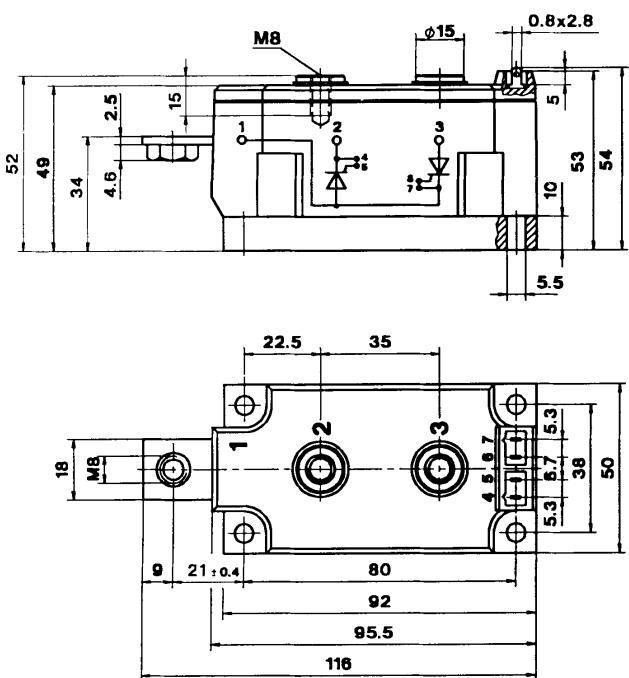


**SKKT 210, SKKT 250**

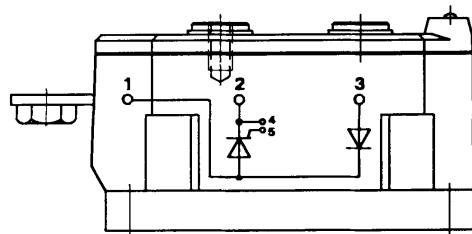
Case A 25

SEMIPACK 3

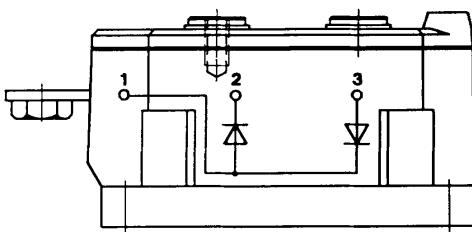
UL recognized, file no. E 63 532

**SKKH 210, SKKH 250**

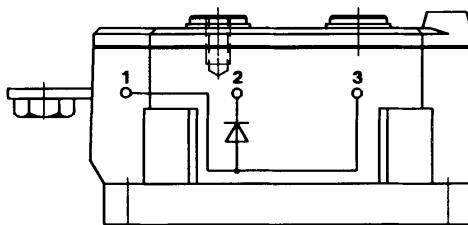
Case A 26

**SKKD 260**

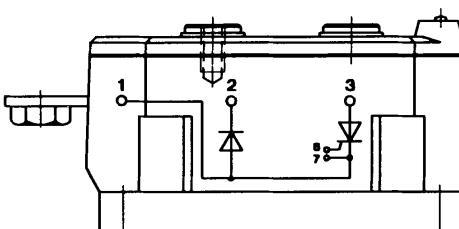
Case A 27

**SKKE 260**

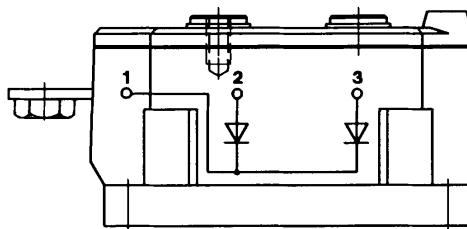
Case A 28

**SKKL 210, SKKL 250**

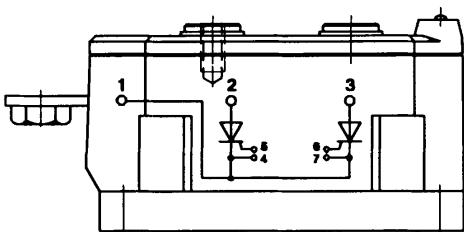
Case A 35

**SKMD 260**

Case A 58

**SKMT 250**

Case A 64



Dimensions in mm